

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S3	3798	parasitic adj (pn (p adj n) diode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 12:49
S4	2176218	substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 12:40
S5	3440055	(resistance resistivity resistor impedance ohm\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 12:40
S6	6128	\$1jfet (\$1j adj fet)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 12:42
S7	2405	(junction adj gate) jugfet (jug adj fet) (jug adj field)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 12:43
S8	1	(S3 and S4 and S5 and (S6 S7)).clm.	US-PGPUB	OR	ON	2006/05/01 12:45
S9	4523	parasit\$3 adj (pn (p adj n) diode junction)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 12:45
S10	1	(S9 and S4 and S5 and (S6 S7)).clm.	US-PGPUB	OR	ON	2006/05/01 12:49
S11	1	(S9 and S5 and (S6 S7)).clm.	US-PGPUB	OR	ON	2006/05/01 12:52
S12	0	(S9 and S4 and S5 and (S6 S7)).clm.	USPAT	OR	ON	2006/05/01 12:46
S13	0	(S9 and S5 and (S6 S7)).clm.	USPAT	OR	ON	2006/05/01 12:47
S14	127929	parasitic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 12:52
S15	2	(S14 and S4 and S5 and (S6 S7)).clm.	US-PGPUB	OR	ON	2006/05/01 14:55
S16	152091	parasit\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 12:52
S17	3	(S16 and S5 and (S6 S7)).clm.	US-PGPUB	OR	ON	2006/05/01 12:54
S18	5	(S16 and S5 and (S6 S7)).clm.	USPAT	OR	ON	2006/05/01 12:54

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L2	263	esd same output near protect\$3 and (mos mosfet fet field adj effect)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 15:23
L3	5	esd same output near protect\$3 and (mos mosfet fet field adj effect) same increase near resistance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 15:24
L4	8	esd same output near protect\$3 and (mos mosfet fet field adj effect) same increase near3 resistance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 15:25
L5	63	esd same output and (mos mosfet fet field adj effect) same increase near3 resistance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 15:26
L6	519	361/90.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 15:31
L7	3121993	(resistance resistivity impedance ohm\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 15:32
L8	2560	7 same (\$1jfet (\$1j adj fet) (junction adj gate) jugfet (jug adj fet) (jug adj field))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 15:34
L9	170	8 same parasit\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 15:38
L10	49	9 same substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 15:34
L11	2506482	protect\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 15:39
L12	65898	11 same (pn diode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 15:39

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L13	2063	12 same parasit\$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 15:39
L14	416	13 same potential	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 15:39
L15	157	14 same substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 15:41
L16	679	13 same substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 15:41
L17	522	16 not 15	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/01 15:41